MOSFETs Silicon N-Channel MOS (π-MOSVII)

TK13E25D

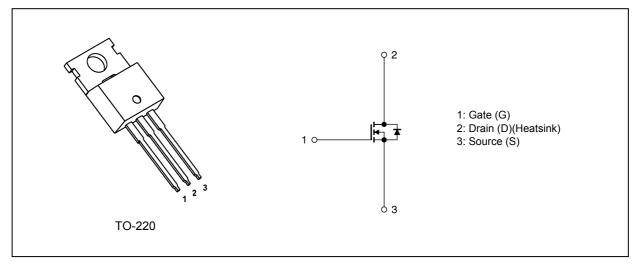
1. Applications

Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.19 \Omega$ (typ.)
- (2) Low leakage current: $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 250 \ V)$
- (3) Enhancement mode: V_{th} = 1.5 to 3.5 V (V_{DS} = 10 V, I_D = 1 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Characteristics			Rating	Unit
Drain-source voltage		V _{DSS}	250	V
Gate-source voltage		V _{GSS}	±20	1
Drain current (DC)	(Note 1)	Ι _D	13	A
Drain current (pulsed)	(Note 1)	I _{DP}	52	1
Power dissipation	(T _c = 25°C)	PD	102	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	78	mJ
Avalanche current	(Note 3)	I _{AR}	13	A
Reverse drain current (DC)	(Note 1)	I _{DR}	13	1
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	52	
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	1

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production 2010-11 2014-01-06

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	1.23	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	83.3	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 50 V, T_{ch} = 25°C (initial), L = 0.77 mH, R_G = 25 Ω , I_{AR} = 13 A

Note 3: Repetitive rating; pulse width limited by maximum channel temperature

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

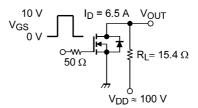
6. Electrical Characteristics

6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V	_	_	±1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 250 V, V _{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	250	_	—	V
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	1.5	—	3.5	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 6.5 A		0.19	0.25	Ω

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 100 V, V _{GS} = 0 V, f = 1 MHz	_	1100	—	pF
Reverse transfer capacitance	C _{rss}		_	8	—	
Output capacitance	C _{oss}		_	66	—	
Gate resistance	r _g	V _{DS} = OPEN, f = 1 MHz	_	5	—	Ω
Switching time (rise time)	t _r	See Figure 6.2.1.	_	40	—	ns
Switching time (turn-on time)	t _{on}		_	55	—	
Switching time (fall time)	t _f		_	20	_	
Switching time (turn-off time)	t _{off}		_	130	_	



Duty \leq 1%, t_W = 10 μs

Fig. 6.2.1 Switching Time Test Circuit

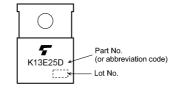
6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 200 \text{ V}, \text{ V}_{GS}$ = 10 V, I _D = 13 A	_	25	—	nC
Gate-source charge 1	Q _{gs1}]	_	4.2	_	
Gate-drain charge	Q _{gd}		_	8.5	_	

6.4. Source-Drain Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

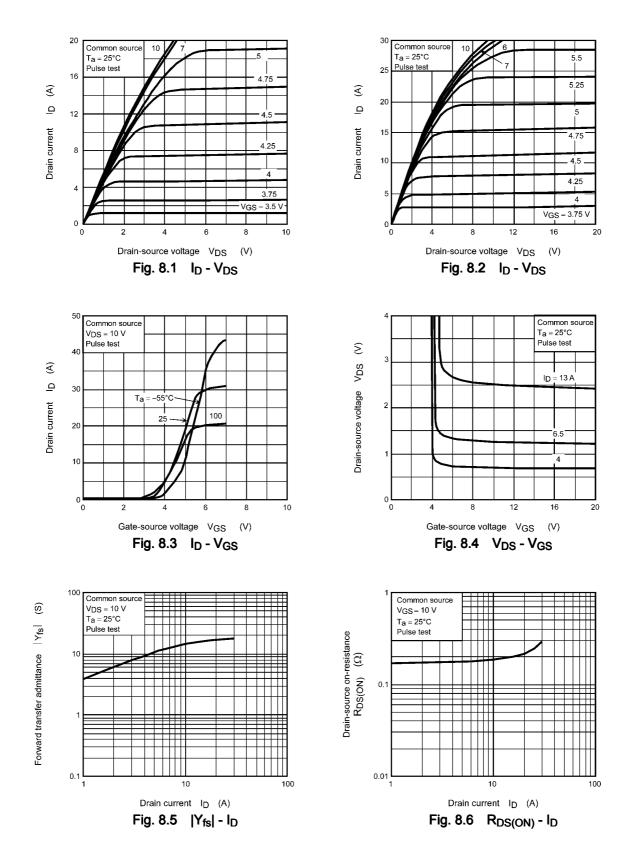
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V _{DSF}	I _{DR} = 13 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 13 A, V _{GS} = 0 V	_	180	—	ns
Reverse recovery charge	Q _{rr}	-dI _{DR} /dt = 100 A/μs		1.1	_	μC
Peak reverse recovery current	١ _m			12	—	А

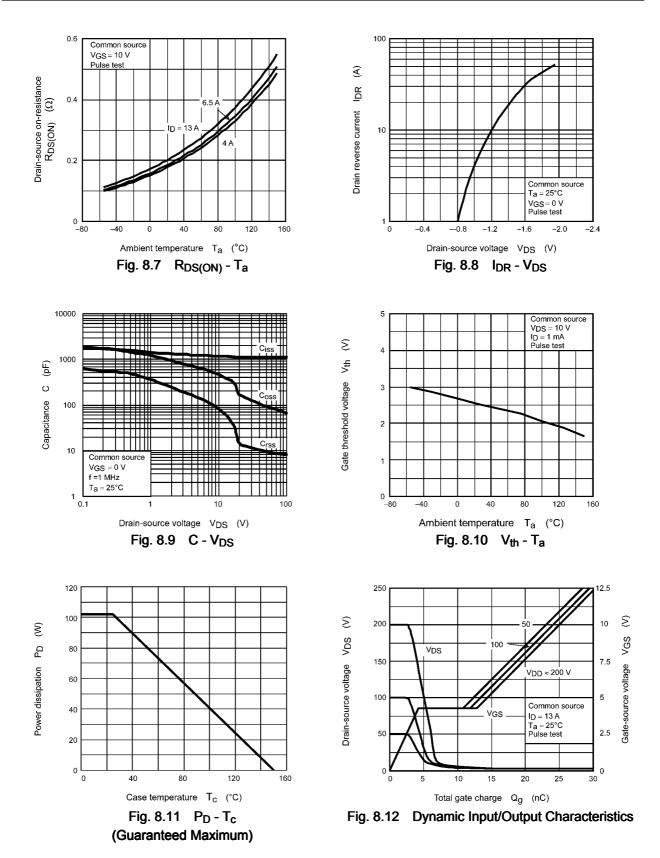
7. Marking

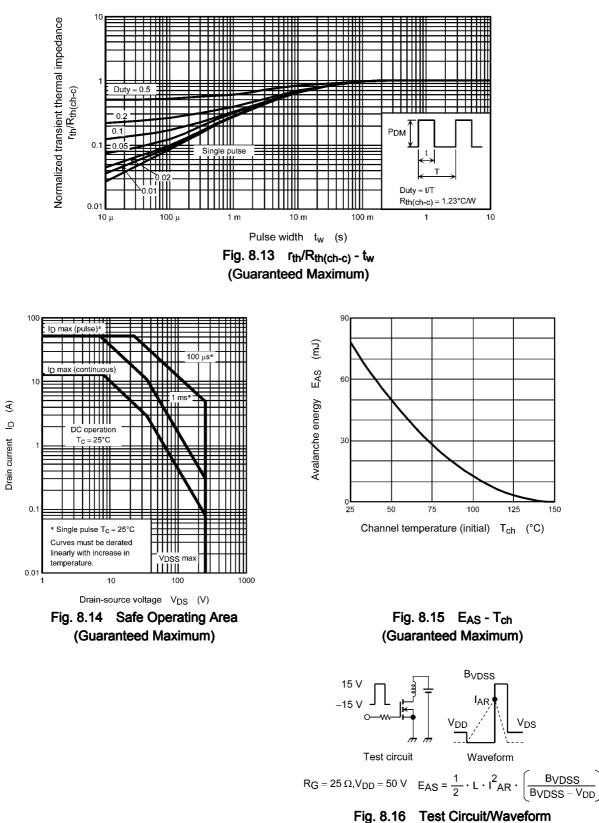




8. Characteristics Curves (Note)







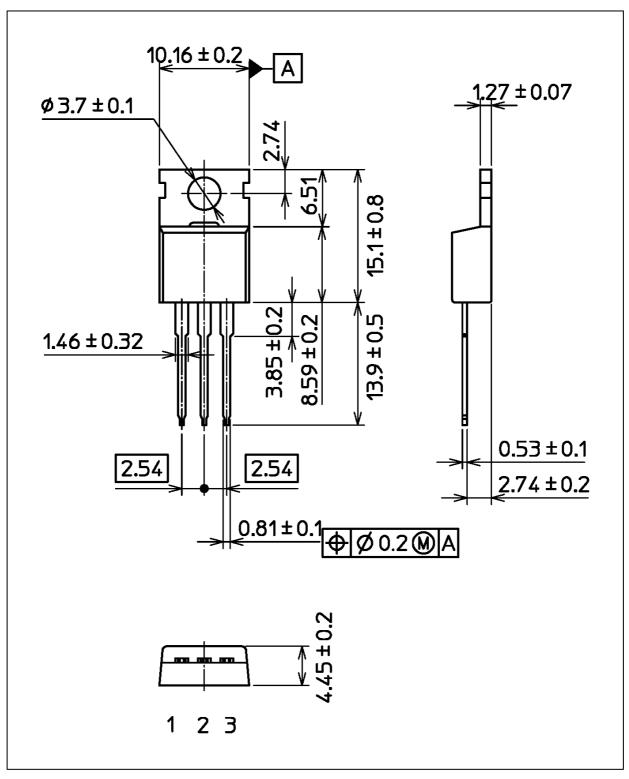
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Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

TK13E25D

Unit: mm



Weight: 1.93 g (typ.)

	Package Name(s)
TOSHIBA: 2-10X1A	
Nickname: TO-220	

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